



IRFR430A, IRFU430A, SiHFR430A, SiHFU430A

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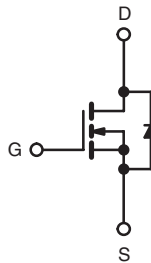
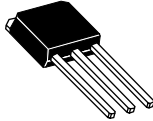
Power MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	500
R _{DS(on)} (Ω)	V _{GS} = 10 V 1.7
Q _g (Max.) (nC)	24
Q _{gs} (nC)	6.5
Q _{gd} (nC)	13
Configuration	Single

DPAK
(TO-252)



IPAK
(TO-251)



N-Channel MOSFET

FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{oss} Specified
- Lead (Pb)-free Available



Available
RoHS*
COMPLIANT

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching

ORDERING INFORMATION					
Package	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	IPAK (TO-251)
Lead (Pb)-free	IRFR430APbF	IRFR430ATRPbF ^a	IRFR430ATRLPbF ^a	IRFR430ATRRPbF ^a	IRFU430APbF
	SiHFR430A-E3	SiHFR430AT-E3 ^a	SiHFR430ATL-E3 ^a	SiHFR430ATR-E3 ^a	SiHFU430A-E3
SnPb	IRFR430A	IRFR430ATR ^a	IRFR430ATRL ^a	IRFR430ATRR ^a	IRFU430A
	SiHFR430A	SiHFR430AT ^a	SiHFR430ATL ^a	SiHFR430ATR ^a	SiHFU430A

Note


a. See device orientation.

ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	500	V	
Gate-Source Voltage	V _{GS}	± 30		
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	A	
		T _C = 100 °C		3.2
Pulsed Drain Current ^a	I _{DM}	20		
Linear Derating Factor		0.91	W/°C	
Single Pulse Avalanche Energy ^b	E _{AS}	130	mJ	
Repetitive Avalanche Current ^a	I _{AR}	5.0	A	
Repetitive Avalanche Energy ^a	E _{AR}	11	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	110	W
Peak Diode Recovery dV/dt ^c		dV/dt	3.0	V/ns
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting T_J = 25 °C, L = 11 mH, R_G = 25 Ω, I_{AS} = 5.0 A (see fig. 12).
- I_{SD} ≤ 5.0 A, dI/dt ≤ 320 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.1	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.60	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.5	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA	
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.0\text{ A}^b$	-	-	1.7	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 3.0\text{ A}$	2.3	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5	-	490	-	pF	
Output Capacitance	C_{oss}		-	75	-		
Reverse Transfer Capacitance	C_{riss}		-	4.5	-		
Output Capacitance	C_{oss}	$V_{GS} = 10\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	750	-	pF
			$V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$	-	25	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$			-	51	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}, I_D = 5.0\text{ A}, V_{DS} = 400\text{ V}$, see fig. 6 and 13 ^b	-	-	24	nC	
Gate-Source Charge	Q_{GS}		-	-	6.5		
Gate-Drain Charge	Q_{GD}		-	-	13		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 5.0\text{ A}, R_G = 15\text{ }\Omega, R_D = 50\text{ }\Omega$, see fig. 10 ^b	-	8.7	-	ns	
Rise Time	t_r		-	27	-		
Turn-Off Delay Time	$t_{d(off)}$		-	17	-		
Fall Time	t_f		-	16	-		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	5.0	A	
Pulsed Diode Forward Current ^a	I_{SM}		-	-	20		
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 5.0\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 5.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	410	620	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	1.4	2.1	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DS} .



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

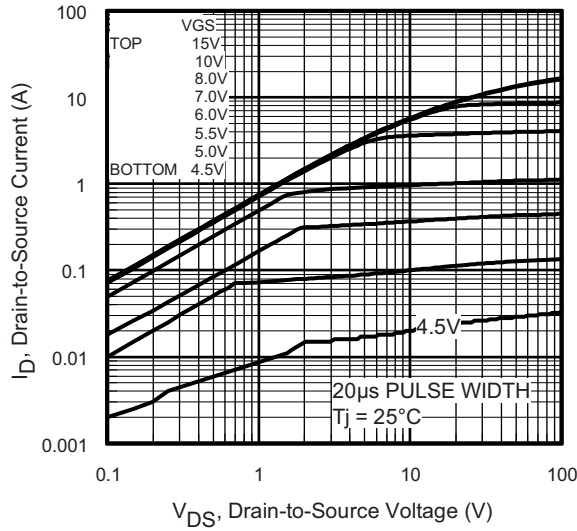


Fig. 1 - Typical Output Characteristics

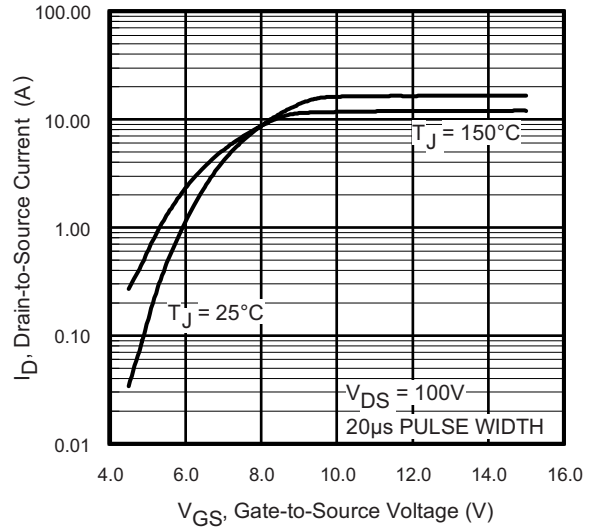


Fig. 3 - Typical Transfer Characteristics

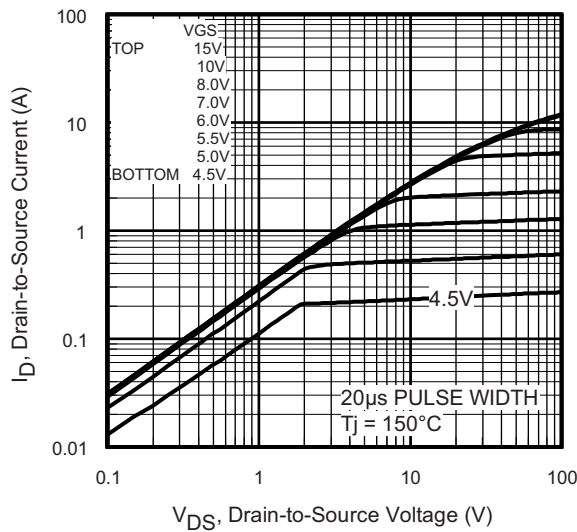


Fig. 2 - Typical Output Characteristics

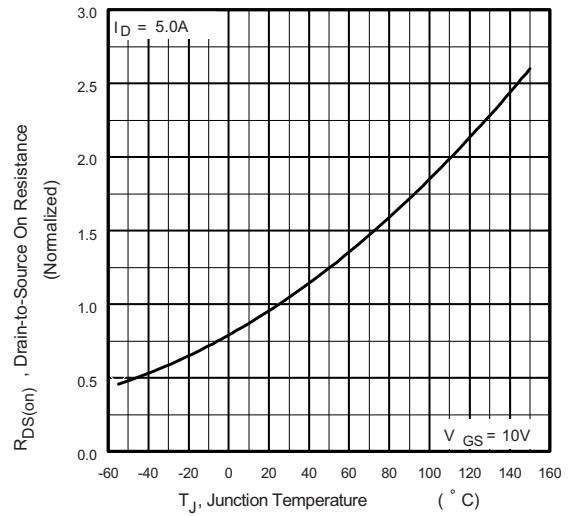


Fig. 4 - Normalized On-Resistance vs. Temperature



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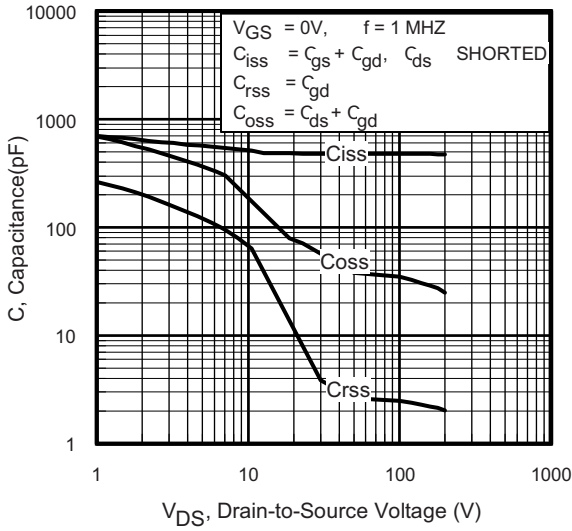


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

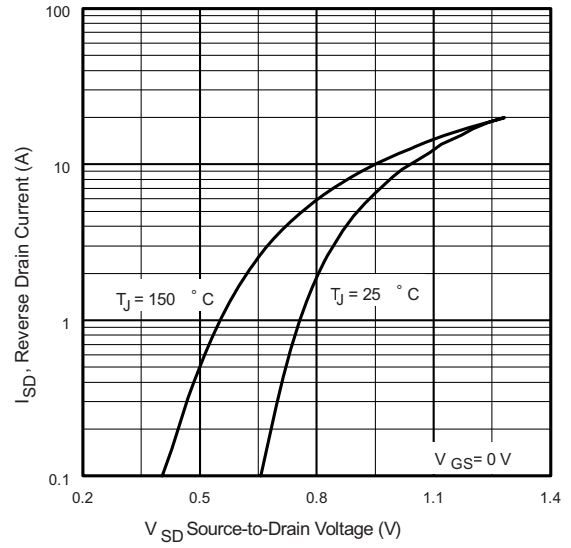


Fig. 7 - Typical Source-Drain Diode Forward Voltage

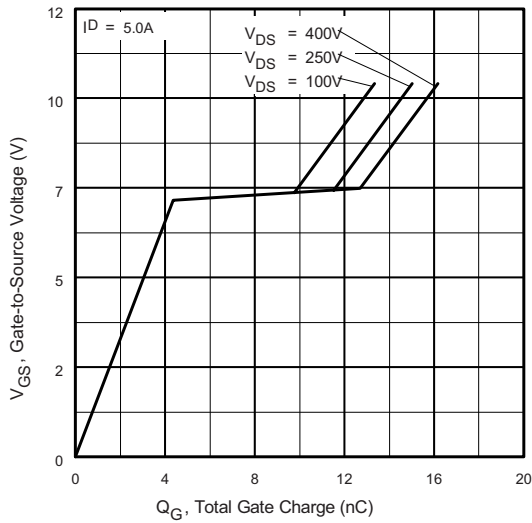


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

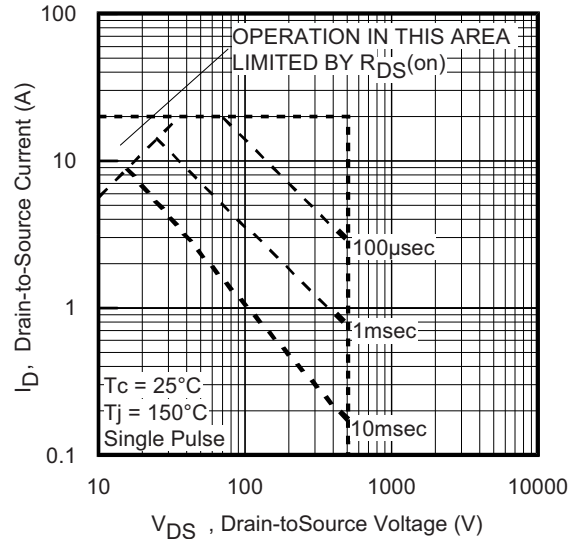


Fig. 8 - Maximum Safe Operating Area



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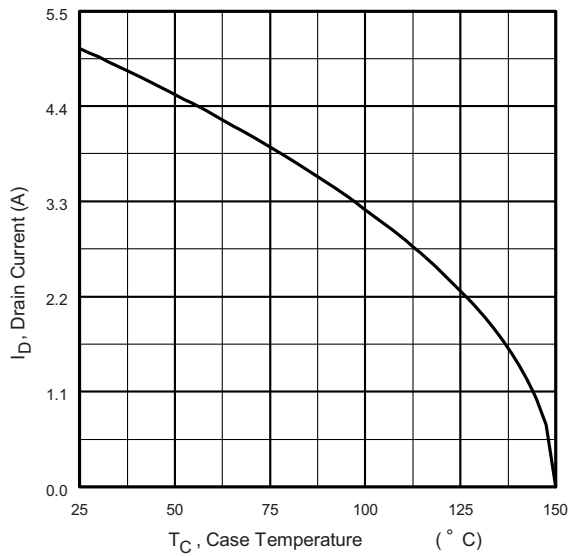


Fig. 9 - Maximum Drain Current vs. Case Temperature

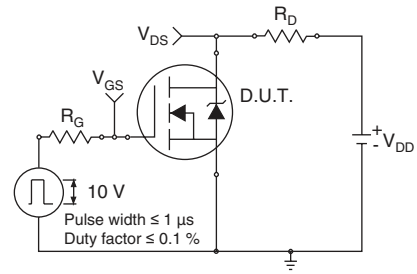


Fig. 10a - Switching Time Test Circuit

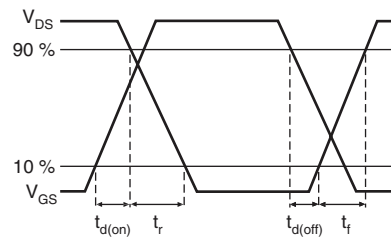


Fig. 10b - Switching Time Waveforms

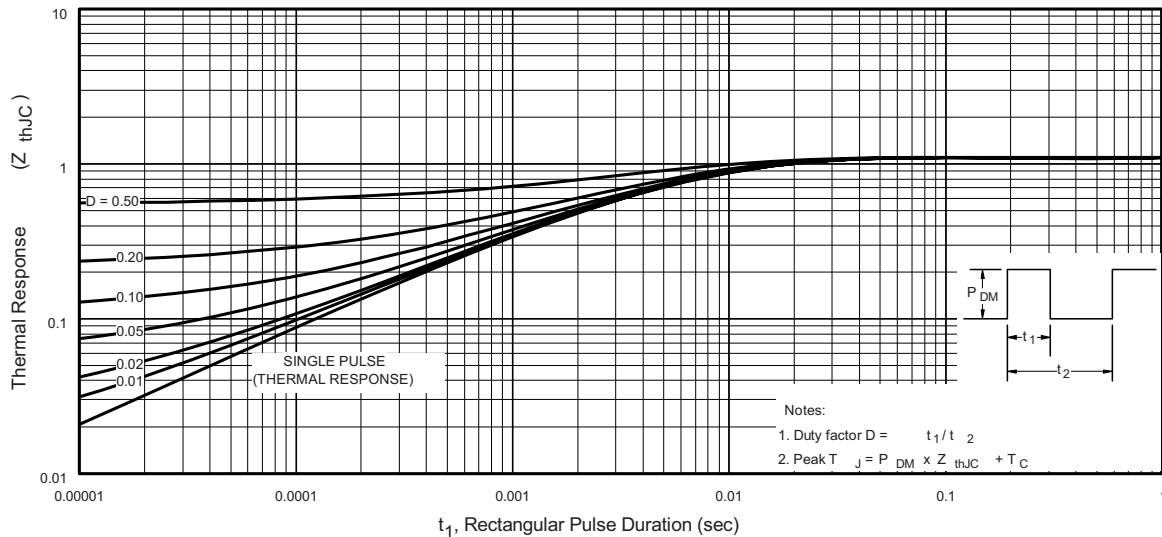


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

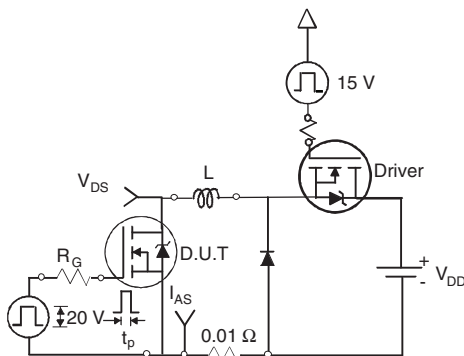


Fig. 12a - Unclamped Inductive Test Circuit

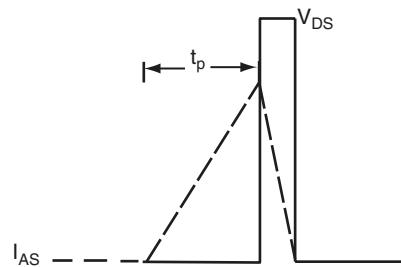


Fig. 12b - Unclamped Inductive Waveforms

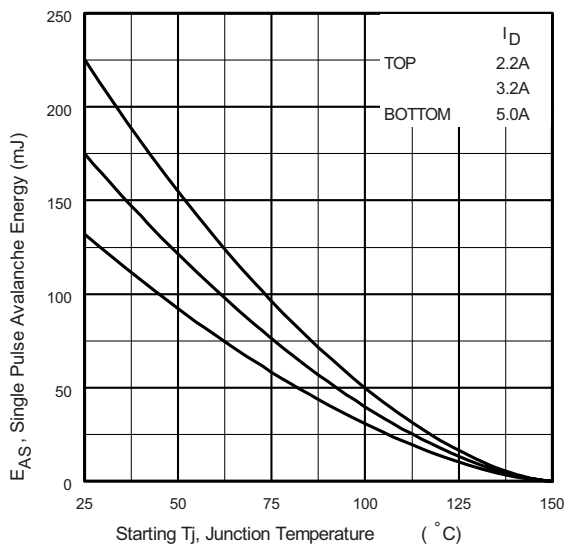


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

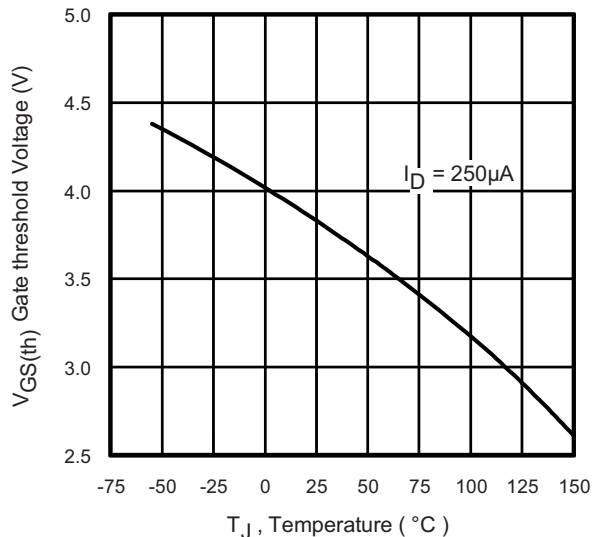


Fig. 12d - Threshold Voltage vs. Temperature

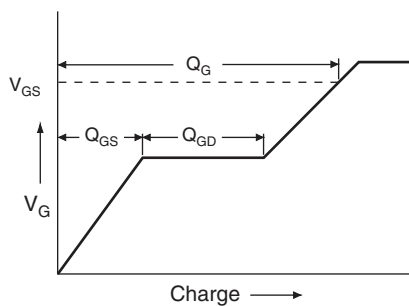


Fig. 13a - Basic Gate Charge Waveform

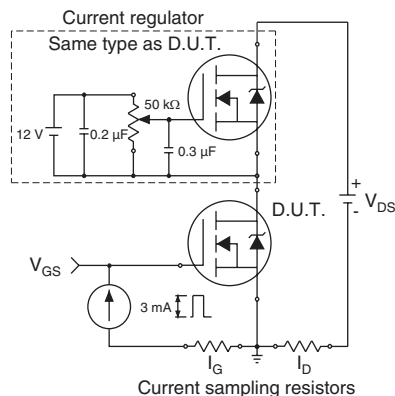


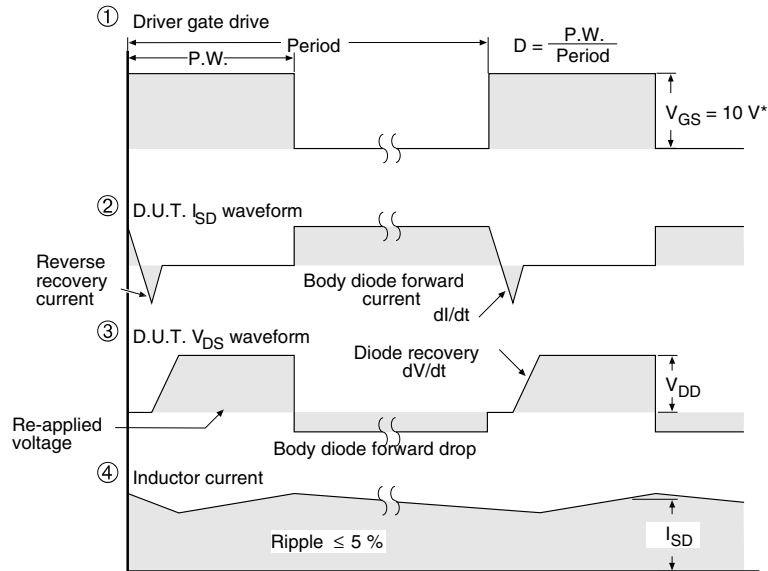
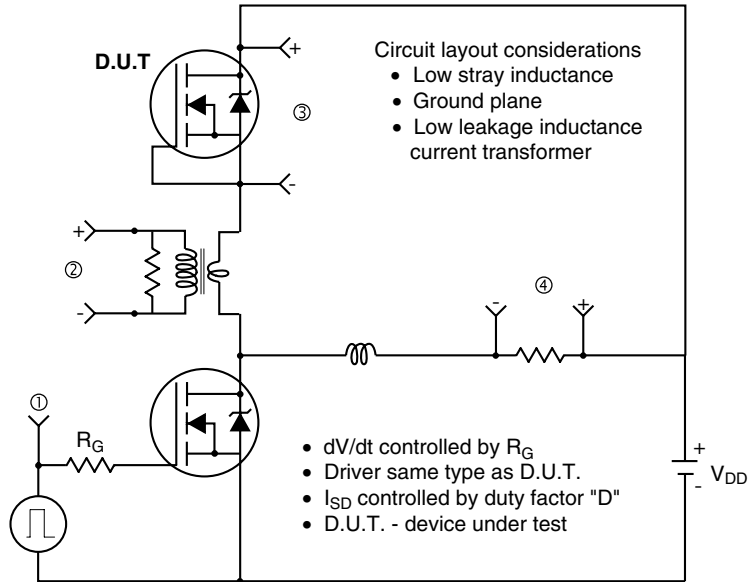
Fig. 13b - Gate Charge Test Circuit



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Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel